



# Bipolar NPN Bare Die – BTN131

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## Part Description

The BTN131 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications. PNP Complement is BTP131

## Key Parameters:

- VCBO = 400V
- VCEO = 350V
- VEBO = 7V
- hFE = 30-333 @ VCE = 10V, IC = 0.01A
- VCE(Sat) = 0.5V @ IC = 0.1A, IB = 10mA
- fT = 100 MHz @ VCE = 30V, IE = 0A
- COBO = - pF @ VCB = - V

## Features

## Die Size (Unseen)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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